

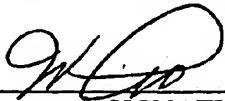


Air Force Invention No. AFB00670

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner of Patents and Trademarks, Washington, D.C. 20231-0001.

On 23 March 2004  
(DATE OF DEPOSIT)

WILLIAM G. AUTON 31,320  
NAME OF APPLICANT, ASSIGNEE, OR REG. REP.

  
SIGNATURE 23 March 2004  
DATE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of  
Richard A. Soref et al  
Application Serial No. 10/722,611  
Filed: 28 November 2003  
For: Strain-engineered Direct-Gap  $\text{Ge/Sn}_x\text{Ge}_{1-x}$  Heterodiode and Multi-Quantum-Well Photodetectors, Lasers, Emitters and Modulators grown on  $\text{Sn}_y\text{Si}_z\text{Ge}_{1-y-z}$  buffered Silicon

Honorable Commissioner of Patents and Trademarks  
Washington D. C. 20231-0001

Sir:

**RESPONSE TO NOTICE TO FILE CORRECTED APPLICATION PAPERS**

In response to the Office Action of 27 February 2004, please consider the following amendment. A fee of \$130 is enclosed.

**IN THE CLAIMS**

Please retain all original claims.

04/07/2004 SZEWDIE1 00000007 010465 10722611

01 FC:1460 130.00 DA

05/24/2004 JNCCHILLA 00000003 010465 10722611

01 FC:1203 290.00 DA